

# **KSA1156**

### High Voltage Switching Low Power Switching Regulator DC-DC Converter

- High Breakdown Voltage
- Low Collector Saturation Voltage
- · High Speed Switching



## **PNP Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector-Base Voltage	- 400	V
V <sub>CEO</sub>	Collector-Emitter Voltage	- 400	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 7	V
I <sub>B</sub>	Base Current	- 0.25	Α
I <sub>C</sub>	Collector Current (DC)	- 0.5	Α
I <sub>CP</sub>	Collector Current (Pulse)	- 1	Α
$P_{C}$	Collector Dissipation (T <sub>a</sub> =25°C)	1	W
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	10	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

# $\textbf{Electrical Characteristics} \ \textbf{T}_{\textbf{C}} = 25 ^{\circ} \textbf{C} \ \text{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = - 100mA, I <sub>B</sub> = - 10mA - 400 L = - 20mH			V
V <sub>CEX</sub> (sus)	Collector-Emitter Sustaining Voltage	$I_C = -200 \text{mA}, I_{B1} = -I_{B2} = -20 \text{mA}$ $V_{BE}(\text{off}) = 5 \text{V}, L = 10 \text{mH}$	- 400		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = - 400V, I <sub>E</sub> = 0		- 100	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = - 5V, I <sub>C</sub> = 0		- 10	μΑ
I <sub>CEX1</sub>	Collector Cut-off Current	V <sub>CE</sub> = - 400V, V <sub>BE</sub> (off) = 1.5V		- 100	μΑ
I <sub>CEX2</sub>	Collector Cut-off Current	$V_{CE} = -400V, V_{BE}(off) = 1.5V$ $T_{C} = 125^{\circ}C$		- 1	mA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = - 5V, I <sub>C</sub> = - 100mA	30	200	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = - 100mA, I <sub>B</sub> = - 10mA		- 1	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = - 100mA, I <sub>B</sub> = - 10mA		- 1.2	V
t <sub>ON</sub>	Turn On Time	V <sub>CC</sub> = - 150V, I <sub>C</sub> = - 100mA		1	μs
t <sub>STG</sub>	Storage Time	$I_{B1} = -10 \text{mA}$ , $I_{B2} = 20 \text{mA}$		4	μs
t <sub>F</sub>	Fall Time	$R_L = 1.5 \text{K}\Omega$		1	μs

# **h**<sub>FE</sub> Classification

h <sub>FF</sub> 30 ~ 60 40 ~ 80 60 ~ 120 100 ~ 2	Classification	N	R	0	Y
	h <sub>FE</sub>	30 ~ 60	40 ~ 80	60 ~ 120	100 ~ 200

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# **Typical Characteristics**

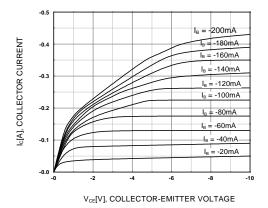


Figure 1. Static Characteristic

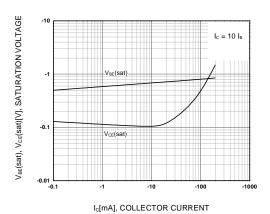


Figure 3. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

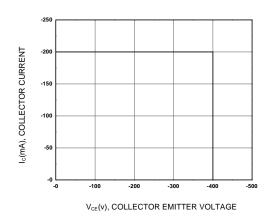


Figure 5. Reverse Bias Safe Operating Area

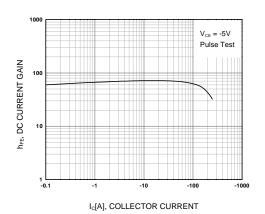


Figure 2. DC current Gain

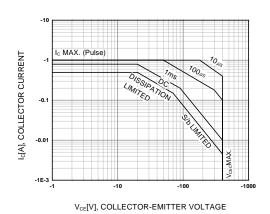


Figure 4. Safe Operating Area

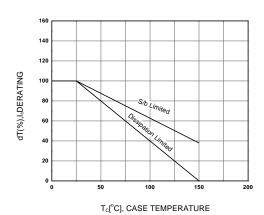


Figure 6. Derating Curve of Safe Operating Areas

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# Typical characteristics (Continued)

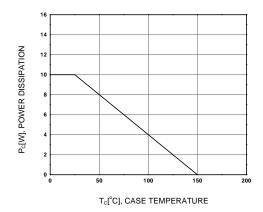
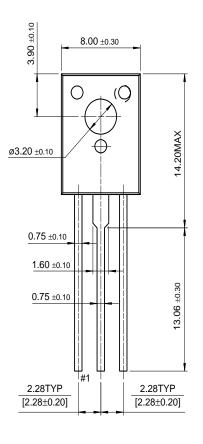


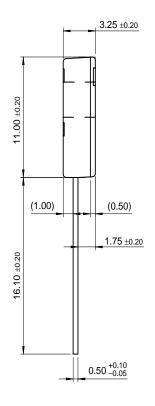
Figure 7. Power Derating

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# **Package Demensions**

TO-126





Dimensions in Millimeters

Downloaded from **Elcodis.com** electronic components distributor

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